

DATE: April 2, 2002

SHEET 1 of 1

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Form PTO - 1449 (M dified)

FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE
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INFORMATION DISCLOSURE
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(Use several sheets if necessary)

(37 CFR 1.98 (b))

APPLICANT

R. Ugajin

FILING DATE

April 2, 2002

GROUP

Not yet assigned

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	PATENT NUMBER	ISSUE DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE

FOREIGN PATENT OR PUBLISHED FOREIGN PATENT APPLICATION

	DOCUMENT NUMBER	PUBLIC- ATION DATE	COUNTRY OR PATENT OFFICE	CLASS	SUB CLASS	TRANS- LATION
						YES NO
B1	1 1 1 9 5 8 0 1	21.07.99	JP			*
B2	2001 1 1 8 3 7 9	27.04.01	JP			*

*abstract only

OTHER DOCUMENTS (Including Author, Title, Date, Place of Publication)

C1	H. Isshiki, K. Tanaka and T. Kimura, "Conduction subband formation in (GaSa)m(GaP)n FRACTAL structured atomic-layer-superlattice grown by atomic layer epitaxy", Proc. of the 24 th International Conference on The Physics of Semiconductors, CD-ROM File No. 0948, World Scientific Publishing Co. (1999)
C2	R. Ugajin, "Composite nanomaterials based on fractal-shaped structures", Physics Letters A, 227, (2000) Pages 267 to 272.

EXAMINER

DATE CONSIDERED

EXAMINER: Initial citation c nsidered. Draw line thr ough citation if n t in conformance and not c nsidered. Include copy f this form with next communicati n to applicant.

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